

C1  
cont

a contact formed within a contact hole between the wiring layer and the substrate,  
the contact electrically connecting the wiring layer to the first diffused layer and a side wall  
of the gate electrode.

C2

4. (Twice Amended) A semiconductor device, comprising:  
a gate electrode formed on a substrate through a gate insulating film;  
a diffused layer formed on the substrate;  
a wiring layer formed above the gate electrode; and  
a contact formed within a contact hole between the wiring layer and the substrate,  
the contact electrically connecting the wiring layer to the diffused layer and a side wall of  
the gate electrode,

D1

wherein the diffused layer has first and second portions formed opposite to each  
other across the portion of the substrate existing under the gate electrode and having a first  
conduction type, each having a second conduction type different from the first conduction  
type of the portion of the substrate; and a third portion that connects the first portion to the  
second portion.

C3

12. (Amended) A semiconductor device according to claim 4, comprising a  
source area and a drain area formed opposed to each other across the channel portion of the  
substrate existing under the gate electrode, and a transistor for composing a semiconductor  
IC therein, wherein the impurity concentration of the diffused layer is higher than the  
impurity concentration of the source area and the drain area.